

DOCKET NO. 00-643/1D
Preliminary Amendment
August 29, 2003

Express Mailing Label No. ET532833503US

In the Specification:

On page 1, lines 1-4, please amend the title to read: "A LOW DIELECTRIC CONSTANT FLUORINE AND CARBON-CONTAINING SILICON OXIDE DIELECTRIC MATERIAL CHARACTERIZED BY IMPROVED RESISTANCE TO OXIDATION".

Please insert the following on page 1, after line 5:

This application is a division of U.S. Patent Application Serial No. 09/792,691 filed February 23, 2001.

Please replace the paragraph beginning at page 1, line 6, with the following further amended paragraph:

The subject matter of this application relates to the subject matter of ~~coexisting~~ U.S. Patent 6,572,925 ~~docket number 00-445~~, entitled "A PROCESS FOR FORMING A LOW DIELECTRIC CONSTANT FLUORINE AND CARBON-CONTAINING SILICON OXIDE DIELECTRIC MATERIAL CHARACTERIZED BY IMPROVED RESISTANCE TO OXIDATION", assigned to the assignee of this application, and filed on the same date as the parent application of this application.

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Please replace the paragraph beginning at page 1, line 11, with the following further amended paragraph:

The subject matter of this application relates to the subject matter of copending U.S. Patent Application Serial No. 09/792,685 ~~docket number 00-446~~, entitled "A PROCESS FOR FORMING A LOW DIELECTRIC CONSTANT FLUORINE AND CARBON-CONTAINING SILICON OXIDE DIELECTRIC MATERIAL CHARACTERIZED BY IMPROVED RESISTANCE TO OXIDATION", assigned to the assignee of this application, and filed on the same date as the parent application of this application.

Please replace the paragraph beginning at page 1, line 16, with the following further amended paragraph:

The subject matter of this application relates to the subject matter of ~~copending~~ U.S. Patent ~~Application Serial No. 6,365,528, issued April 2, 2002~~ ~~09/590,310, filed on June 7, 2000~~, entitled "A LOW TEMPERATURE PROCESS FOR FORMING A LOW DIELECTRIC CONSTANT FLUORINE AND CARBON-CONTAINING SILICON OXIDE DIELECTRIC MATERIAL CHARACTERIZED BY IMPROVED RESISTANCE TO OXIDATION AND GOOD GAP-FILLING CAPABILITIES", and assigned to the assignee of this application.

Please replace the paragraph beginning at page 9, line 1, with the following further amended paragraph:

Where R_1 is a 3 to 5 carbon organo moiety, R_1 will often be a saturated alkyl and contain more secondary hydrogen atoms than primary hydrogen atoms. While not intending to be limited by the following theory, it is thought that secondary hydrogen atoms are more susceptible to oxidation relative to primary hydrogen atoms. This susceptibility to oxidation is described in detail in U.S. Patent No. 6,303,047, issued October 16, 2001 ~~Application 09/274,457~~, which is incorporated herein by reference. Accordingly, when R_1 contains more secondary hydrogen atoms than primary hydrogen atoms, R_1 may have an increased propensity for cleavage when reacted with an oxidizing agent in the process of the invention. When R_1 is a saturated alkyl, R_1 has more secondary hydrogens than primary hydrogens when R_1 contains 3 or more carbon atoms (e.g., a $-\text{CH}_2\text{-CH}_2\text{-CH}_3$ moiety has four secondary hydrogens and three primary hydrogens). Similarly, tertiary hydrogens are considered to be more sensitive to oxidation than are secondary hydrogens. Accordingly, in one embodiment it may be desirable for R_1 to contain at least one tertiary hydrogen (e.g., $-\text{CH}(\text{CH}_3)_2$).

Please replace the paragraph beginning at page 19, line 29, with the following further amended paragraph:

Similarly, the low k fluorine and carbon-containing silicon oxide dielectric material formed in the method of the invention may find utility, for example, as one or more of the low k dielectric layers described in U.S. Patent Nos. 6,423,628, issued July 23, 2002; 6,232,658, issued May 15, 2001; 6,391,795, issued May 21, 2002; 6,492,731, issued December 10, 2002; 6,350,700, issued February 26, 2002; 6,423,630, issued July 23, 2002; and 6,537,923, issued March 25,